

**General Purpose NPN Epitaxial Planar Transistor**

# BTC1815A3

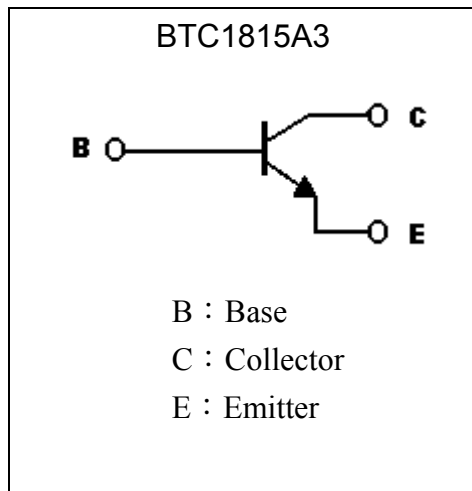
## Description

The BTC1815A3 is designed for use in driver stage of AF amplifier and low speed switching.

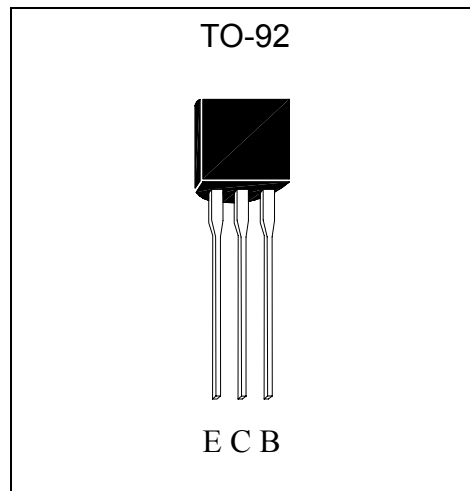
## Features

- High voltage and high current :  $V_{CEO}=50V(\text{min}), I_C=150mA(\text{max})$
- High  $H_{FE}$  and excellent linearity
- Complementary to BTA1015A3

## Symbol



## Outline



## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	50	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	150	mA
Base Current	$I_B$	50	mA
Power Dissipation @Ta=25°C	$P_d$	400	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	250	°C/W
Junction Temperature	$T_j$	125	°C
Storage Temperature	$T_{stg}$	-55~+125	°C



**Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
$BV_{CBO}$	60	-	-	V	$I_C=100\mu A$
$BV_{CEO}$	50	-	-	V	$I_C=1mA$
$BV_{EBO}$	5	-	-	V	$I_E=10\mu A$
$I_{CBO}$	-	-	100	nA	$V_{CB}=60V$
$I_{EBO}$	-	-	100	nA	$V_{EB}=5V$
* $V_{CE(sat)}$	-	-	0.25	V	$I_C=100mA, I_B=10mA$
* $V_{BE(sat)}$	-	-	1.0	V	$I_C=100mA, I_B=10mA$
$h_{FE1}$	70	-	700	-	$V_{CE}=6V, I_C=2mA$
$h_{FE2}$	25	100	-	-	$V_{CE}=6V, I_C=150mA$
$f_T$	80	-	-	MHz	$V_{CE}=10V, I_C=1mA$
Cob	-	-	3.5	pF	$V_{CB}=10V, I_E=0, f=1MHz$

\*Pulse Test: Pulse Width  $\leq 380\mu s$ , Duty Cycle  $\leq 2\%$

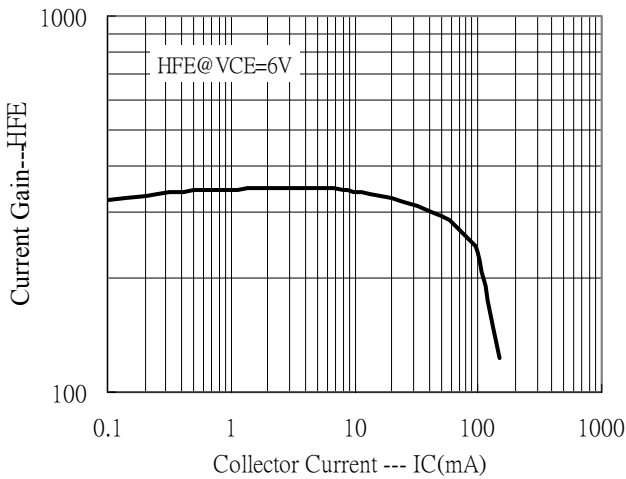
**Classification of  $h_{FE} 1$**

Rank	O	Y	GR	BL
Range	70~140	120~240	200~400	350~700

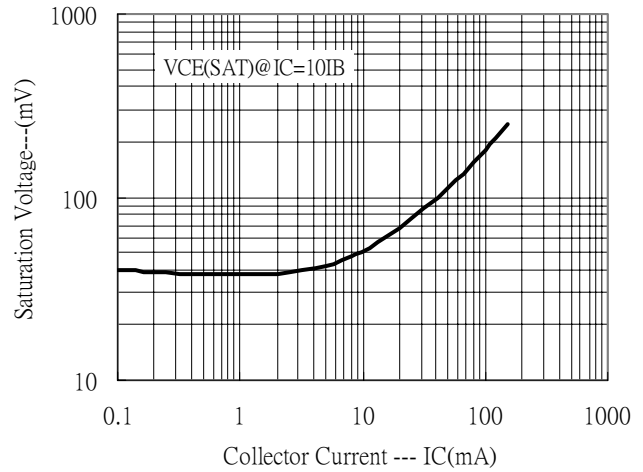


### Characteristic Curves

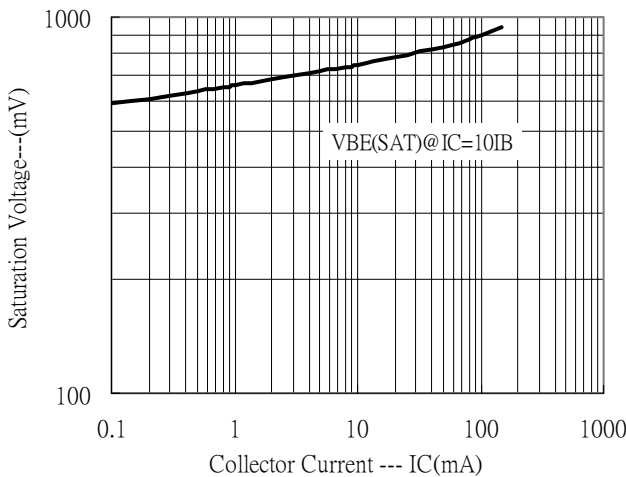
Current Gain vs Collector Current



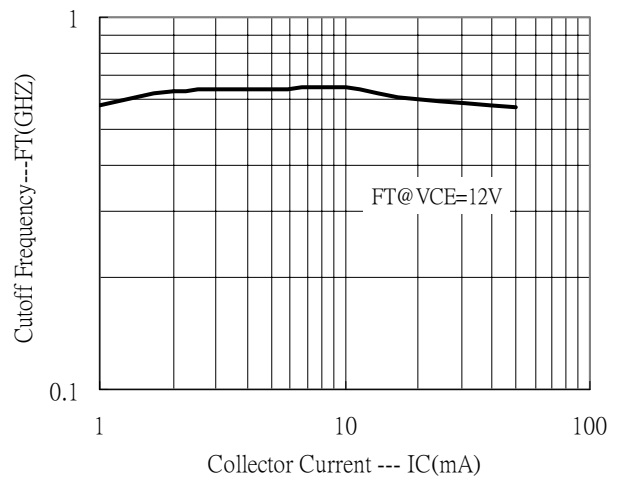
Saturation Voltage vs Collector Current



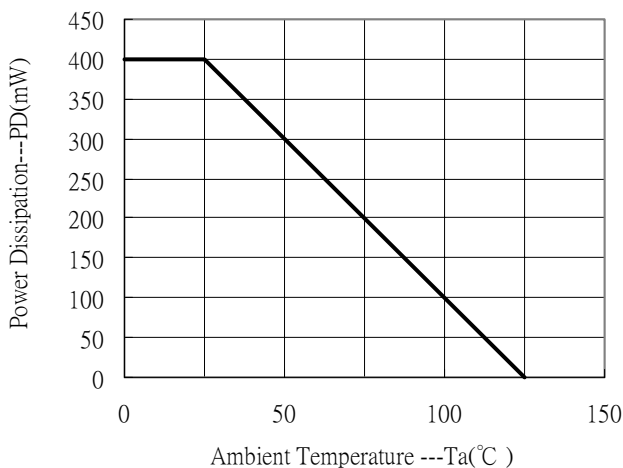
Saturation Voltage vs Collector Current



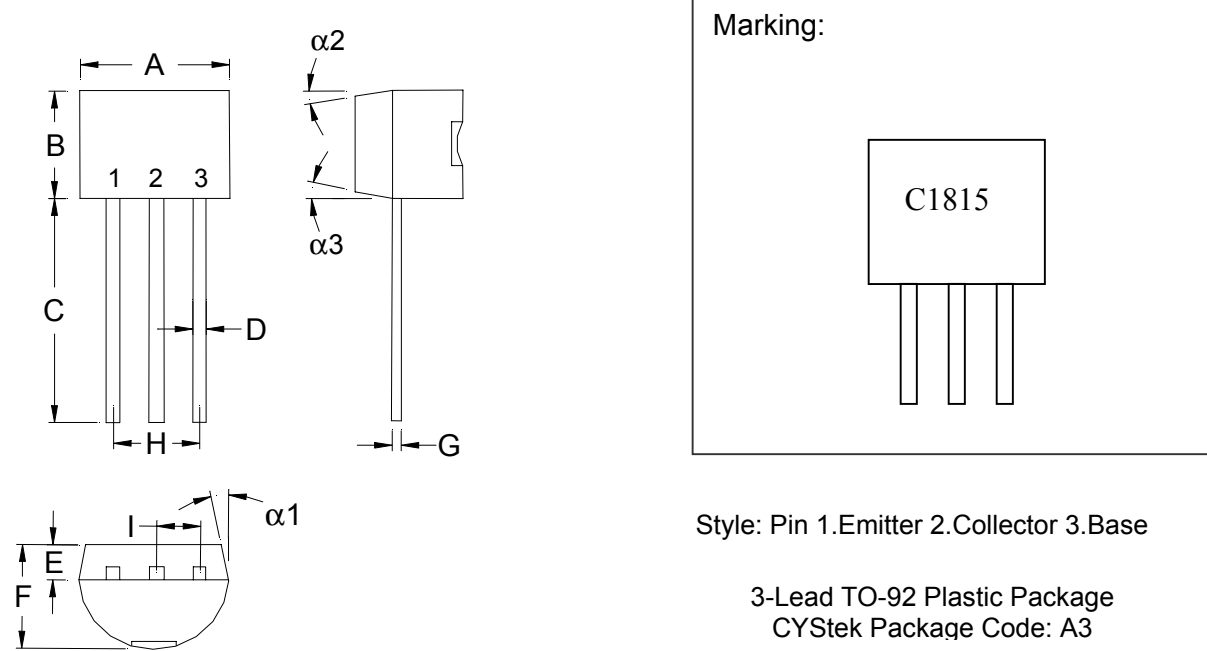
Cutoff Frequency vs Collector Current



Power Derating Curve



**TO-92 Dimension**



Marking:

Style: Pin 1. Emitter 2. Collector 3. Base

3-Lead TO-92 Plastic Package  
 CYStek Package Code: A3

\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1704	0.1902	4.33	4.83	G	0.0142	0.0220	0.36	0.56
B	0.1704	0.1902	4.33	4.83	H	-	*0.1000	-	*2.54
C	0.5000	-	12.70	-	I	-	*0.0500	-	*1.27
D	0.0142	0.0220	0.36	0.56	$\alpha 1$	-	*5°	-	*5°
E	-	*0.0500	-	*1.27	$\alpha 2$	-	*2°	-	*2°
F	0.1323	0.1480	3.36	3.76	$\alpha 3$	-	*2°	-	*2°

Notes: 1. Controlling dimension: millimeters.  
 2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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